Sergey A Dvoretskiy

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

28 2,409 40 203 h-index g-index citations papers 216 2,984 2.2 4.72 L-index ext. citations avg, IF ext. papers

#	Paper	IF	Citations
203	Engineering topological phases in triple HgTe/CdTe quantum wells Scientific Reports, 2022, 12, 2617	4.9	O
202	Edge and Bulk Transport in a Two-Dimensional Topological Insulator Based on a CdHgTe Quantum Well. <i>JETP Letters</i> , 2022 , 115, 202-207	1.2	О
201	Generation of Terahertz Radiation in InP:Fe Crystals Due to Second-Order Lattice Nonlinearity. Semiconductors, 2021 , 55, 785	0.7	
200	Toward Peltier-cooled mid-infrared HgCdTe lasers: Analyzing the temperature quenching of stimulated emission at ~6 fh wavelength from HgCdTe quantum wells. <i>Journal of Applied Physics</i> , 2021 , 130, 214302	2.5	1
199	Mid-IR stimulated emission in Hg(Cd)Te/CdHgTe quantum well structures up to 200 K due to suppressed Auger recombination. <i>Laser Physics</i> , 2021 , 31, 015801	1.2	2
198	Photothermal Ionization Spectroscopy of Mercury Vacancies in HgCdTe Epitaxial Films. <i>JETP Letters</i> , 2021 , 113, 402-408	1.2	О
197	Auger recombination in narrow gap HgCdTe/CdHgTe quantum well heterostructures. <i>Journal of Applied Physics</i> , 2021 , 129, 133106	2.5	4
196	Distinction between electron states formed at topological insulator interfaces with the trivial phase and vacuum. <i>Scientific Reports</i> , 2021 , 11, 11638	4.9	
195	Terahertz Magnetospectroscopy of Cyclotron Resonances from Topological Surface States in Thick Films of CdxHg1\(\text{\text{IT}} \)E. <i>Physica Status Solidi (B): Basic Research</i> , 2021 , 258, 2000023	1.3	5
194	Multiple crossings of Landau levels of two-dimensional fermions in double HgTe quantum wells. <i>Physical Review B</i> , 2021 , 103,	3.3	1
193	Express Characterization of the HgCdTe/CdHgTe Quantum Well Waveguide Heterostructures with the Quasi-Relativistic Carrier Dispersion Law by Room-Temperature Photoluminescence Spectroscopy. <i>Technical Physics Letters</i> , 2021 , 47, 154-157	0.7	1
192	THz polarization-dependent response of antenna-coupled HgCdTe photoconductors under an external constant electric field. <i>Semiconductor Science and Technology</i> , 2021 , 36, 105009	1.8	О
191	Non-local terahertz photoconductivity in the topological phase of HgCdTe. <i>Scientific Reports</i> , 2021 , 11, 1587	4.9	3
190	Characterization of Crystal Perfection in the Layers of (013)HgCdTe/CdTe/ZnTe/GaAs Heterostructures via the Second Harmonic Generation Method. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2021 , 57, 458-467	0.6	
189	Effect of Internal Optical Losses on the Generation of Mid-IR Stimulated Emission in Waveguide Heterostructures with HgCdTe/CdHgTe Quantum Wells. <i>Semiconductors</i> , 2021 , 55, 899-902	0.7	
188	Preparation of Atomically Clean and Structurally Ordered Surfaces of Epitaxial CdTe Films for Subsequent Epitaxy. <i>Semiconductors</i> , 2021 , 55, S62-S66	0.7	0
187	Magneto-intersubband oscillations in two-dimensional systems with an energy spectrum split due to spin-orbit interaction. <i>Physical Review B</i> , 2020 , 101,	3.3	2

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186	Two-dimensional topological insulator state in double HgTe quantum well. <i>Physical Review B</i> , 2020 , 101,	3.3	5
185	Density of states measurements for the heavy subband of holes in HgTe quantum wells. <i>Physical Review B</i> , 2020 , 101,	3.3	1
184	Apparent PT-symmetric terahertz photoconductivity in the topological phase of HgCdTe-based structures. <i>Scientific Reports</i> , 2020 , 10, 2377	4.9	7
183	Possibilities of Characterizing the Crystal Parameters of CdxHg1 IxTe Structures on GaAs Substrates by the Method of Generation of the Probe-Radiation Second Harmonic in Reflection Geometry. <i>Physics of the Solid State</i> , 2020 , 62, 252-259	0.8	3
182	HgCdTe-Based 640	0.5	1
181	Symmetry breaking and circular photogalvanic effect in epitaxial CdxHg1NTe films. <i>Physical Review Materials</i> , 2020 , 4,	3.2	10
180	Quantum Hall effect and Landau levels in the three-dimensional topological insulator HgTe. <i>Physical Review Research</i> , 2020 , 2,	3.9	7
179	Investigation of Stimulated Emission from HgTe/CdHgTe Quantum-Well Heterostructures in the 35 fb Atmospheric Transparency Window. <i>Semiconductors</i> , 2020 , 54, 1365-1370	0.7	
178	Mid-infrared stimulated emission in HgCdTe/CdHgTe quantum well heterostructures at room temperature. <i>Optical Engineering</i> , 2020 , 60,	1.1	2
177	Effects of the ElectronElectron Interaction in the Magneto-Absorption Spectra of HgTe/CdHgTe Quantum Wells with an Inverted Band Structure. <i>JETP Letters</i> , 2020 , 112, 508-512	1.2	O
176	Molecular Beam Epitaxy of CdHgTe: Current State and Horizons. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2020 , 56, 456-469	0.6	2
175	Topological insulators based on HgTe. <i>Physics-Uspekhi</i> , 2020 , 63, 629-647	2.8	5
174	Investigation of the Photosensitivity of Narrow-Gap and Gapless HgCdTe Solid Solutions in the Terahertz and Sub-Terahertz Range. <i>Semiconductors</i> , 2020 , 54, 1096-1102	0.7	О
173	Anisotropy of the in-plane g-factor of electrons in HgTe quantum wells. <i>Physical Review B</i> , 2020 , 101,	3.3	1
172	Unconventional reentrant quantum Hall effect in a HgTe/CdHgTe double quantum well. <i>Physical Review B</i> , 2020 , 102,	3.3	2
171	Effective Mass and g-Factor of Two-Dimentional HgTe B -Band Electrons: Shubnikov-de Haas Oscillations. <i>Semiconductors</i> , 2020 , 54, 982-990	0.7	O
170	Many-particle effects in optical transitions from zero-mode Landau levels in HgTe quantum wells. <i>Physical Review B</i> , 2020 , 102,	3.3	2
169	Probing States of a Double Acceptor in CdHgTe Heterostructures via Optical Gating. <i>JETP Letters</i> , 2020 , 111, 575-581	1.2	2

168	Transport Features in the Topological Phase Hg0.87Cd0.13Te under Terahertz Photoexcitation. <i>Semiconductors</i> , 2020 , 54, 1064-1068	0.7	
167	Continuous-Wave Stimulated Emission in the 10🛮 4-th Range under Optical Excitation in HgCdTe/CdHgTe-QW Structures with Quasirelativistic Dispersion. <i>Semiconductors</i> , 2020 , 54, 1371-1375	0.7	1
166	Magnetic Susceptibility Measurements in HgTe Quantum Wells in a Perpendicular Magnetic Field. JETP Letters, 2020 , 111, 633-638	1.2	2
165	TEM studies of structural defects in HgTe/HgCdTe quantum wells. <i>Applied Nanoscience</i> (Switzerland), 2020 , 10, 2867-2871	3.3	2
164	Impact Ionization Induced by Terahertz Radiation in HgTe Quantum Wells of Critical Thickness. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2020 , 41, 1155-1169	2.2	1
163	Second-Harmonic Generation of Subterahertz Gyrotron Radiation by Frequency Doubling in InP:Fe and Its Application for Magnetospectroscopy of Semiconductor Structures. <i>Semiconductors</i> , 2019 , 53, 1217-1221	0.7	4
162	Evolution of the Impurity Photoconductivity in CdHgTe Epitaxial Films with Temperature. <i>Semiconductors</i> , 2019 , 53, 1266-1271	0.7	1
161	Study of the Auger Recombination Energy Threshold in a Series of Waveguide Heterostructures with HgTe/Cd0.7Hg0.3Te QWs Near 14 lb. <i>Semiconductors</i> , 2019 , 53, 1154-1157	0.7	4
160	Determining the Compositional Profile of HgTe/CdxHg1 IxTe Quantum Wells by Single-Wavelength Ellipsometry. <i>Optics and Spectroscopy (English Translation of Optika I Spektroskopiya)</i> , 2019 , 127, 340-346	0.7	8
159	A Megapixel Matrix Photodetector of the Middle Infrared Range. <i>Journal of Communications Technology and Electronics</i> , 2019 , 64, 1011-1015	0.5	2
158	Spin splitting of surface states in HgTe quantum wells. Low Temperature Physics, 2019, 45, 159-164	0.7	3
157	Topological surface states in thick partially relaxed HgTe films. <i>Physical Review B</i> , 2019 , 99,	3.3	8
156	Magnetoabsorption in HgCdTe/CdHgTe Quantum Wells in Tilted Magnetic Fields. <i>JETP Letters</i> , 2019 , 109, 191-197	1.2	1
155	High-frequency impact ionization and nonlinearity of photocurrent induced by intense terahertz radiation in HgTe-based quantum well structures. <i>Physical Review B</i> , 2019 , 99,	3.3	2
154	Experimental Observation of Temperature-Driven Topological Phase Transition in HgTe/CdHgTe Quantum Wells. <i>Condensed Matter</i> , 2019 , 4, 27	1.8	2
153	Features of Photoluminescence of Double Acceptors in HgTe/CdHgTe Heterostructures with Quantum Wells in a Terahertz Range. <i>JETP Letters</i> , 2019 , 109, 657-662	1.2	6
152	Suppressed Auger scattering and tunable light emission of Landau-quantized massless Kane electrons. <i>Nature Photonics</i> , 2019 , 13, 783-787	33.9	8
151	Topological Protection Brought to Light by the Time-Reversal Symmetry Breaking. <i>Physical Review Letters</i> , 2019 , 123, 056801	7.4	11

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150	An Optical Study of Disordering in Cadmium Mercury Telluride Solid Solutions. <i>Technical Physics Letters</i> , 2019 , 45, 553-556	0.7	О
149	Magneto-transport in inverted HgTe quantum wells. Npj Quantum Materials, 2019, 4,	5	9
148	On the Thermal Activation of Conductivity Electrons in a p-Type HgTe/CdHgTe Double Quantum Well with HgTe Layers of Critical Width. <i>Semiconductors</i> , 2019 , 53, 919-922	0.7	3
147	Residual-Photoconductivity Spectra in HgTe/CdHgTe Quantum-Well Heterostructures. <i>Semiconductors</i> , 2019 , 53, 1363-1366	0.7	2
146	Photodetectors with 384 🛮 288 Matrix Elements for the Infrared Range of 8🗓 0 Microns. <i>Journal of Communications Technology and Electronics</i> , 2019 , 64, 1024-1029	0.5	3
145	Express Characterization of Crystalline Perfection of CdxHg1\(\mathbb{I}\)Te Structures by Reflection Second Harmonic Generation of Probing Radiation. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2019 , 55, 447-454	0.6	2
144	Features of Magneto-Intersubband Oscillations in HgTe Quantum Wells. JETP Letters, 2019, 110, 301-3	05 .2	5
143	Shubnikovde Haas Oscillations in a Three-Dimensional Topological Insulator Based on a Strained HgTe Film in an Inclined Magnetic Field. <i>JETP Letters</i> , 2019 , 109, 799-805	1.2	2
142	Landau level spectroscopy of valence bands in HgTe quantum wells: effects of symmetry lowering. Journal of Physics Condensed Matter, 2019 , 31, 145501	1.8	10
141	Temperature-Induced Topological Phase Transition in HgTe Quantum Wells. <i>Physical Review Letters</i> , 2018 , 120, 086401	7.4	28
140	Probing spin helical surface states in topological HgTe nanowires. <i>Physical Review B</i> , 2018 , 97,	3.3	32
139	Stimulated emission in the 2.8-3.5 h wavelength range from Peltier cooled HgTe/CdHgTe quantum well heterostructures. <i>Optics Express</i> , 2018 , 26, 12755-12760	3.3	18
138	Electron Effective Mass and g Factor in Wide HgTe Quantum Wells. Semiconductors, 2018, 52, 12-18	0.7	2
137	Magnetooptical Studies and Stimulated Emission in Narrow Gap HgTe/CdHgTe Structures in the Very Long Wavelength Infrared Range. <i>Semiconductors</i> , 2018 , 52, 436-441	0.7	
136	Transmission Spectra of HgTe-Based Quantum Wells and Films in the Far-Infrared Range. <i>Physics of the Solid State</i> , 2018 , 60, 778-782	0.8	1
135	Terahertz Photoluminescence of Double Acceptors in Bulky Epitaxial HgCdTe Layers and HgTe/CdHgTe Structures with Quantum Wells. <i>Journal of Experimental and Theoretical Physics</i> , 2018 , 127, 1125-1129	1	4
134	Advanced Design of Scanning Infrared Focal Plane Arrays. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2018 , 54, 569-575	0.6	O
133	Terahertz Cyclotron Photoconductivity in a Highly Unbalanced Two-Dimensional Electron⊞ole System. <i>JETP Letters</i> , 2018 , 108, 247-252	1.2	5

132	Bipolar Persistent Photoconductivity in HgTe/CdHgTe (013) Double Quantum-Well Heterostructures. <i>Semiconductors</i> , 2018 , 52, 1586-1589	0.7	5
131	Polarization-Sensitive Fourier-Transform Spectroscopy of HgTe/CdHgTe Quantum Wells in the Far Infrared Range in a Magnetic Field. <i>JETP Letters</i> , 2018 , 108, 329-334	1.2	2
130	HgCdTe based quantum well heterostructures for long-wavelength lasers operating in 5 - 15 THz range. <i>Journal of Physics: Conference Series</i> , 2018 , 1092, 012126	0.3	
129	Magnetoconductivity and Terahertz Response of a HgCdTe Epitaxial Layer. <i>Sensors</i> , 2018 , 18,	3.8	3
128	Two-dimensional semimetal in HgTe quantum well under hydrostatic pressure. <i>Physical Review B</i> , 2018 , 98,	3.3	1
127	Magnetooptics of HgTe/CdTe Quantum Wells with Giant Rashba Splitting in Magnetic Fields up to 34 T. <i>Semiconductors</i> , 2018 , 52, 1386-1391	0.7	O
126	Radiative recombination in narrow gap HgTe/CdHgTe quantum well heterostructures for laser applications. <i>Journal of Physics Condensed Matter</i> , 2018 , 30, 495301	1.8	10
125	Effect of Features of the Band Spectrum on the Characteristics of Stimulated Emission in Narrow-Gap Heterostructures with HgCdTe Quantum Wells. <i>Semiconductors</i> , 2018 , 52, 1375-1379	0.7	4
124	Non-equilibrium electron transport induced by terahertz radiation in the topological and trivial phases of Hg Cd Te. <i>Beilstein Journal of Nanotechnology</i> , 2018 , 9, 1035-1039	3	10
123	Electrical Properties of the V-Defects of Epitaxial HgCdTe. <i>Journal of Electronic Materials</i> , 2017 , 46, 44	435 <u>r4</u> 431	8
123	Electrical Properties of the V-Defects of Epitaxial HgCdTe. <i>Journal of Electronic Materials</i> , 2017 , 46, 46. Activation transport under quantum Hall regime in HgTe-based heterostructure. <i>Low Temperature Physics</i> , 2017 , 43, 485-490	435£4 ; 438 0.7	3
	Activation transport under quantum Hall regime in HgTe-based heterostructure. <i>Low Temperature</i>		
122	Activation transport under quantum Hall regime in HgTe-based heterostructure. <i>Low Temperature Physics</i> , 2017 , 43, 485-490	0.7	3
122	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490 HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, 035503 Polarization Pyrometry of Layered Semiconductor Structures under Conditions of Low-Temperature Technological Processes. Optoelectronics, Instrumentation and Data Processing,	o.7 5.7	3
122 121 120	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490 HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, 035503 Polarization Pyrometry of Layered Semiconductor Structures under Conditions of Low-Temperature Technological Processes. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 630-638	0.7 5.7 0.6	3 33 2
122 121 120	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490 HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, 035503 Polarization Pyrometry of Layered Semiconductor Structures under Conditions of Low-Temperature Technological Processes. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 630-638 Robust helical edge transport at #0 quantum Hall state. Physical Review B, 2017, 96, Valence band energy spectrum of HgTe quantum wells with an inverted band structure. Physical	0.7 5.7 0.6	33326
122 121 120 119	Activation transport under quantum Hall regime in HgTe-based heterostructure. Low Temperature Physics, 2017, 43, 485-490 HgCdTe-based heterostructures for terahertz photonics. APL Materials, 2017, 5, 035503 Polarization Pyrometry of Layered Semiconductor Structures under Conditions of Low-Temperature Technological Processes. Optoelectronics, Instrumentation and Data Processing, 2017, 53, 630-638 Robust helical edge transport at #0 quantum Hall state. Physical Review B, 2017, 96, Valence band energy spectrum of HgTe quantum wells with an inverted band structure. Physical Review B, 2017, 96, Photogalvanic probing of helical edge channels in two-dimensional HgTe topological insulators.	0.7 5.7 0.6 3.3	3332622

(2016-2017)

114	On the band spectrum in p-type HgTe/CdHgTe heterostructures and its transformation under temperature variation. <i>Semiconductors</i> , 2017 , 51, 1531-1536	0.7	5	
113	Terahertz Photoconductivity in $Hg1$ Cd x Te near the transition from the direct to inverted spectrum. <i>JETP Letters</i> , 2017 , 106, 162-166	1.2	10	
112	Stimulated emission from HgCdTe quantum well heterostructures at wavelengths up to 19.5 lb. <i>Applied Physics Letters</i> , 2017 , 111, 192101	3.4	44	
111	Temperature-driven single-valley Dirac fermions in HgTe quantum wells. <i>Physical Review B</i> , 2017 , 96,	3.3	23	
110	Terahertz photoconductivity of double acceptors in narrow gap HgCdTe epitaxial films grown by molecular beam epitaxy on GaAs(013) and Si(013) substrates. <i>Semiconductor Science and Technology</i> , 2017 , 32, 095007	1.8	17	
109	Investigation of HgCdTe waveguide structures with quantum wells for long-wavelength stimulated emission. <i>Semiconductors</i> , 2017 , 51, 1557-1561	0.7	6	
108	Investigation of the surface-potential distribution of epitaxial CdHgTe films. <i>Journal of Surface Investigation</i> , 2016 , 10, 1096-1100	0.5	1	
107	The noise model of CTIA-based pixel of SWIR HgCdTe focal plane arrays 2016 ,		2	
106	Magnetotransport in double quantum well with inverted energy spectrum: HgTe/CdHgTe. <i>Physical Review B</i> , 2016 , 93,	3.3	13	
105	Spin-orbit splitting of valence and conduction bands in HgTe quantum wells near the Dirac point. <i>Physical Review B</i> , 2016 , 93,	3.3	28	
104	Probing Quantum Capacitance in a 3D Topological Insulator. <i>Physical Review Letters</i> , 2016 , 116, 166802	7.4	34	
103	Methodological and instrumental problems in high-precision in situ ellipsometry diagnostics of the mercury cadmium telluride layer composition in molecular beam epitaxy. <i>Instruments and Experimental Techniques</i> , 2016 , 59, 857-864	0.5	4	
102	Magnetospectroscopy of double HgTe/CdHgTe quantum wells. Semiconductors, 2016, 50, 1532-1538	0.7	8	
101	Temperature-driven massless Kane fermions in HgCdTe crystals. <i>Nature Communications</i> , 2016 , 7, 1257	617.4	47	
100	Zeeman splitting of the conduction band of HgTe quantum wells with a semimetallic spectrum. <i>JETP Letters</i> , 2016 , 104, 241-247	1.2	4	
99	Cell of the silicon integrated reading circuit with built-it analog-digital converter. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2016 , 52, 381-387	0.6		
98	Defects in mercury-cadmium telluride heteroepitaxial structures grown by molecular-beam epitaxy on silicon substrates. <i>Semiconductors</i> , 2016 , 50, 208-211	0.7	2	
97	Observation of topological phase transition by terahertz photoconductivity in HgTe-based transistors. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016 , 13, 534-537		2	

96	CdHgTe heterostructures for new-generation IR photodetectors operating at elevated temperatures. <i>Semiconductors</i> , 2016 , 50, 1626-1629	0.7	4
95	Capacitance spectroscopy of a system of gapless Dirac fermions in a HgTe quantum well. <i>JETP Letters</i> , 2016 , 104, 859-863	1.2	8
94	Long-wavelength stimulated emission and carrier lifetimes in HgCdTe-based waveguide structures with quantum wells. <i>Semiconductors</i> , 2016 , 50, 1651-1656	0.7	7
93	Long wavelength stimulated emission up to 9.5 fb from HgCdTe quantum well heterostructures. <i>Applied Physics Letters</i> , 2016 , 108, 092104	3.4	25
92	Weak antilocalization in a three-dimensional topological insulator based on a high-mobility HgTe film. <i>JETP Letters</i> , 2016 , 104, 302-308	1.2	3
91	Mercury vacancies as divalent acceptors in Hg y Te1 Iy /Cd x Hg1 Ik Te structures with quantum wells. <i>Semiconductors</i> , 2016 , 50, 1662-1668	0.7	5
90	HgTe/CdHgTe double quantum well with a spectrum of bilayer graphene and peculiarities of its magnetotransport. <i>JETP Letters</i> , 2016 , 104, 403-410	1.2	9
89	Quantum hall effect in a system of gapless Dirac fermions in HgTe quantum wells. <i>JETP Letters</i> , 2015 , 100, 724-730	1.2	12
88	Three-dimensional topological insulator based on a strained HgTe film. <i>Low Temperature Physics</i> , 2015 , 41, 82-89	0.7	3
87	Surface states in a HgTe quantum well and scattering by surface roughness. <i>JETP Letters</i> , 2015 , 101, 330-333	1.2	5
86	Anticrossing of Landau levels in HgTe/CdHgTe (013) quantum wells with an inverted band structure. <i>JETP Letters</i> , 2015 , 100, 790-794	1.2	23
85	Energy spectrum and transport in narrow HgTe quantum wells. Semiconductors, 2015, 49, 39-43	0.7	2
84	Acceptor states in heteroepitaxial CdHgTe films grown by molecular-beam epitaxy. <i>Semiconductors</i> , 2015 , 49, 367-372	0.7	9
83	Persistence of a two-dimensional topological insulator state in wide HgTe quantum wells. <i>Physical Review Letters</i> , 2015 , 114, 126802	7.4	48
82	Conductance of a lateral pl junction in two-dimensional HgTe structures with an inverted spectrum: The role of edge states. <i>JETP Letters</i> , 2015 , 101, 469-473	1.2	1
81	Exchange enhancement of the electron g-factor in a two-dimensional semimetal in HgTe quantum wells. <i>Semiconductors</i> , 2015 , 49, 1627-1633	0.7	5
80	Shot noise of the edge transport in the inverted band HgTe quantum wells. <i>JETP Letters</i> , 2015 , 101, 708	J- 7 .13	20
79	Evidence on the macroscopic length scale spin coherence for the edge currents in a narrow HgTe quantum well. <i>JETP Letters</i> , 2015 , 101, 814-819	1.2	14

(2013-2015)

78	Cyclotron-resonance-assisted photocurrents in surface states of a three-dimensional topological insulator based on a strained high-mobility HgTe film. <i>Physical Review B</i> , 2015 , 92,	3.3	61
77	Analysis of charge-carrier diffusion in the photosensing films of HgCdTe infrared focal plane array photodetectors. <i>Journal of Applied Physics</i> , 2015 , 118, 124508	2.5	6
76	Terahertz detection of magnetic field-driven topological phase transition in HgTe-based transistors. <i>Applied Physics Letters</i> , 2015 , 107, 152101	3.4	10
75	Investigation of possibility of VLWIR lasing in HgCdTe based heterostructures. <i>Journal of Physics: Conference Series</i> , 2015 , 647, 012008	0.3	3
74	Temperature scaling in the quantum-Hall-effect regime in a HgTe quantum well with an inverted energy spectrum. <i>Semiconductors</i> , 2015 , 49, 1545-1549	0.7	9
73	Investigation of magnetoabsorption at different temperatures in HgTe/CdHgTe quantum-well heterostructures in pulsed magnetic fields. <i>Semiconductors</i> , 2015 , 49, 1611-1615	0.7	5
72	Metal-insulator transition in a HgTe quantum well under hydrostatic pressure. <i>JETP Letters</i> , 2014 , 98, 843-847	1.2	14
71	Photoluminescence of CdHgTe solid solutions subjected to low-energy ion treatment. <i>Semiconductors</i> , 2014 , 48, 195-198	0.7	4
70	Observation of three-dimensional massless Kane fermions in a zinc-blende crystal. <i>Nature Physics</i> , 2014 , 10, 233-238	16.2	143
69	Efficient long wavelength interband photoluminescence from HgCdTe epitaxial films at wavelengths up to 26 fh. <i>Applied Physics Letters</i> , 2014 , 104, 072102	3.4	28
68	Time resolved photoluminescence spectroscopy of narrow gap Hg1\(\mathbb{L}\)CdxTe/CdyHg1\(\mathbb{J}\)Te quantum well heterostructures. <i>Applied Physics Letters</i> , 2014 , 105, 022102	3.4	23
67	Hole transport and valence-band dispersion law in a HgTe quantum well with a normal energy spectrum. <i>Physical Review B</i> , 2014 , 89,	3.3	14
66	Transport properties of a 3D topological insulator based on a strained high-mobility HgTe film. <i>Physical Review Letters</i> , 2014 , 112, 196801	7:4	56
65	Temperature dependence of the resistance of a two-dimensional topological insulator in a HgTe quantum well. <i>Physical Review B</i> , 2014 , 89,	3.3	53
64	Terahertz electron transport in a two-dimensional topological insulator in a HgTe quantum well. <i>JETP Letters</i> , 2014 , 99, 290-294	1.2	7
63	Determination of charge-carrier diffusion length in the photosensing layer of HgCdTe n-on-p photovoltaic infrared focal plane array detectors. <i>Applied Physics Letters</i> , 2014 , 104, 092112	3.4	6
62	Giant photocurrents in a Dirac fermion system at cyclotron resonance. <i>Physical Review B</i> , 2013 , 87,	3.3	55
61	Increasing the mechanical strength of hybrid photodetectors based on mercury-cadmium-telluride heteroepitaxial layers. <i>Optoelectronics, Instrumentation and Data Processing</i> , 2013 , 49, 94-100	0.6	1

60	Dual-wavelength stimulated emission from a double-layer Cd x Hg1 lk Te structure at wavelengths of 2 and 3 lh. <i>JETP Letters</i> , 2013 , 97, 358-361	1.2	1
59	Weak localization of Dirac fermions in HgTe quantum wells. <i>JETP Letters</i> , 2013 , 96, 730-734	1.2	22
58	High-temperature photoluminescence of CdHgTe solid solutions grown by molecular-beam epitaxy. <i>Technical Physics</i> , 2013 , 58, 1536-1539	0.5	4
57	Photoluminescence of HgCdTe nanostructures grown by molecular beam epitaxy on GaAs. <i>Opto-electronics Review</i> , 2013 , 21,	2.4	6
56	Specific features of the spectra and relaxation kinetics of long-wavelength photoconductivity in narrow-gap HgCdTe epitaxial films and heterostructures with quantum wells. <i>Semiconductors</i> , 2013 , 47, 1438-1441	0.7	15
55	The effect of electron-hole scattering on transport properties of a 2D semimetal in the HgTe quantum well. <i>Journal of Experimental and Theoretical Physics</i> , 2013 , 117, 933-943	1	9
54	Two-dimensional semimetal in wide HgTe quantum wells: Charge-carrier energy spectrum and magnetotransport. <i>Semiconductors</i> , 2013 , 47, 1562-1566	0.7	3
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